

isc Silicon NPN Power Transistor

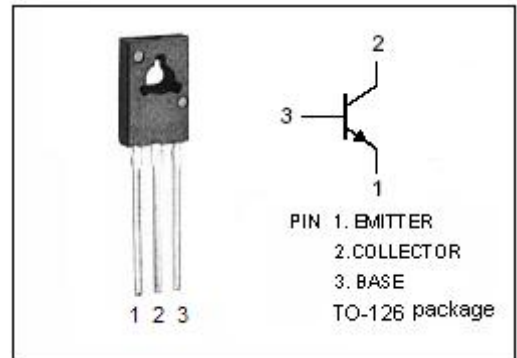
MJE182G

DESCRIPTION

- Collector–Emitter Sustaining Voltage—
: $V_{CEO(SUS)} = 80\text{ V}$
- DC Current Gain—
: $h_{FE} = 30(\text{Min}) @ I_C = 0.5\text{ A}$
= $12(\text{Min}) @ I_C = 1.5\text{ A}$
- Complement to the PNP MJE172G
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

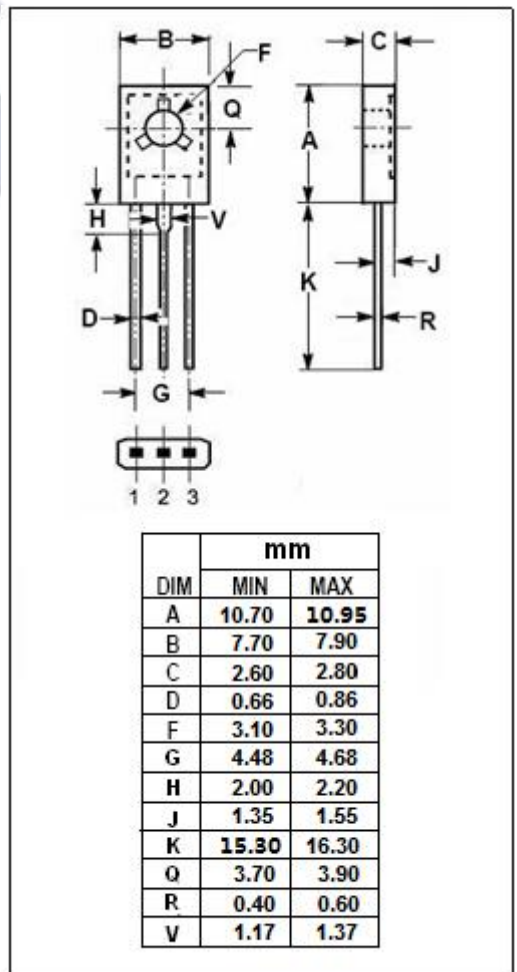
APPLICATIONS

- Low power audio amplifier
- Low current high speed switching applications



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	100	V
V _{CEO}	Collector-Emitter Voltage	80	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current-Continuous	3	A
I _{CM}	Collector Current-peak	6	A
I _B	Base Current	1	A
P _C	Collector Power Dissipation T _a =25°C	1.5	W
	Collector Power Dissipation T _C =25°C	12.5	
T _i	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-65~150	°C



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	10	°C/W
R _{th j-a}	Thermal Resistance, Junction to Ambient	83.4	°C/W

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ELECTRICAL CHARACTERISTICS

 $T_C = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = 10\text{mA}; I_B = 0$	80		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = 0.5\text{A}; I_B = 50\text{mA}$		0.3	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = 1.5\text{A}; I_B = 0.15\text{A}$		0.9	V
$V_{CE(sat)-3}$	Collector-Emitter Saturation Voltage	$I_C = 3\text{A}; I_B = 0.6\text{A}$		1.7	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	$I_C = 1.5\text{A}; I_B = 0.15\text{A}$		1.5	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	$I_C = 3\text{A}; I_B = 0.6\text{A}$		2.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 1\text{V}; I_C = 0.5\text{A}$		1.2	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 100\text{V}; I_E = 0$ $V_{CB} = 100\text{V}; I_E = 0; T_C = 150^\circ\text{C}$		0.1 0.1	μA mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 7\text{V}; I_C = 0$		0.1	μA
h_{FE-1}	DC Current Gain	$I_C = 0.1\text{A}; V_{CE} = 1\text{V}$	50	250	
h_{FE-2}	DC Current Gain	$I_C = 0.5\text{A}; V_{CE} = 1\text{V}$	30		
h_{FE-3}	DC Current Gain	$I_C = 1.5\text{A}; V_{CE} = 1\text{V}$	12		
f_T	Current-Gain—Bandwidth Product	$I_C = 0.1\text{A}; V_{CE} = 10\text{V};$	30		MHz
C_{OB}	Collector Capacitance	$I_E = 0; V_{CB} = 10\text{V}; f_{test} = 0.1\text{MHz}$	40		pF

G:Pb-Free Package